

Please amend the above-captioned patent application, without prejudice, as follows:

IN THE SPECIFICATION:

On Page 1, please insert the following paragraph on 1 after the Title and the paragraph entitled “TECHNICAL FIELD”:

--RELATED APPLICATIONS

The present invention is related to the following co-pending patent applications: Serial No. 10/026,016 entitled “Vertical cavity surface emitting laser including indium, antimony and nitrogen in the active region,” filed December 20, 2001; Serial No. 10/026,020 entitled “Vertical cavity surface emitting laser including indium and antimony in the active region,” filed December 27, 2001; Serial No. 10/026,044 entitled “Indium free vertical cavity surface emitting laser,” filed December 27, 2001; and Serial No. 10/026,055 entitled “Vertical cavity surface emitting laser including indium in the active region,” filed December 27, 2001.--

On Page 16, replace the second full paragraph providing textual reference to Figure 12 with the following paragraph:

--Referring to Figure 12, illustrated is a sectional view of a vertical cavity surface emitting laser **100** (VCSEL). The VCSEL **100** can be grown by techniques such as metal organic molecular beam epitaxy, or metal-organic chemical vapor deposition. Reference is made to U.S. Patent No. 5,903,588, assigned to the assignee for the present invention, which describes methods of VCSEL fabrication use in the art. The VCSEL can preferably be grown on a GaAs substrate **101** due to the robust nature and low cost of the material, however it should be recognized that semiconductor materials, Ge for example, could also be used as the substrate. The VCSEL **100** can then be formed by disposing layers on the substrate.--